

L Number	Hits	Search Text	DB	Time stamp
1	4	6211094.URPN.	USPAT	2004/07/11 12:30
2	5	("3627569"   "5131752"   "5318632"   "5800616"   "6054181").PN.	USPAT	2004/07/11 12:36
3	71	5131752.URPN.	USPAT	2004/07/11 12:43
4	4	6211094.URPN.	USPAT	2004/07/11 12:51
5	5	("3627569"   "5131752"   "5318632"   "5800616"   "6054181").PN.	USPAT	2004/07/11 12:54
6	17	5503707.URPN.	USPAT	2004/07/11 13:03
7	4	("4198261"   "5131752"   "5160576"   "5270222").PN.	USPAT	2004/07/11 13:04
8	0	5300313.URPN.	USPAT	2004/07/11 13:08
9	0	5300313.URPN.	USPAT	2004/07/11 13:09
10	5	("2726173"   "4427711"   "4466872"   "5131752"   "5204144").PN.	USPAT	2004/07/11 13:09
11	8	("3158675"   "4105338"   "4649261"   "4695162"   "4698486"   "4837603"   "4850711"   "4906844").PN.	USPAT	2004/07/11 13:10
16	3525	method with control with thickness with (film layer)	USPAT; US-PGPUB; EPO; JPO	2004/07/11 14:18
17	205	(method with control with thickness with (film layer)) and determining and comparing	USPAT; US-PGPUB; EPO; JPO	2004/07/11 14:27
18	136	((method with control with thickness with (film layer)) and determining and comparing) and (wafer semiconductor)	USPAT; US-PGPUB; EPO; JPO	2004/07/11 14:26
19	86	((method with control with thickness with (film layer)) and determining and comparing) and (wafer semiconductor)) and adjusting	USPAT; US-PGPUB; EPO; JPO	2004/07/11 14:22
20	2024	(method with control with thickness with (film layer)) and (wafer semiconductor)	USPAT; US-PGPUB; EPO; JPO	2004/07/11 14:26
21	1823	adjusting same determining same comparing	USPAT; US-PGPUB; EPO; JPO	2004/07/11 14:38
22	2	((method with control with thickness with (film layer)) and (wafer semiconductor)) and (adjusting same determining same comparing)	USPAT; US-PGPUB; EPO; JPO	2004/07/11 14:38